





60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C
60V	$140 \text{m}\Omega$ @ $V_{GS} = 10V$	2.3A
000	170mΩ @ $V_{GS} = 4.5V$	2.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

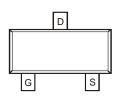
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.0072 grams (Approximate)

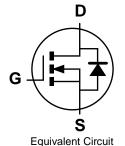








Pin Configuration



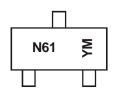
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN6140LQ-7	SOT23	3,000/Tape & Reel
DMN6140LQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- $5.\ For\ packaging\ details,\ go\ to\ our\ website\ at\ http://www.diodes.com/products/packages.html.$

Marking Information



N61 = Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α		3	С		D		Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	1.6 1.2	Α
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	2.0 1.6	Α
Continuous Drain Current (Note 7) // 10//	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.3 1.8	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	2.9 2.3	Α
Maximum Continuous Body Diode Forward Current	I _S	1.5	А		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	10	Α

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 6)	T _A = +25°C	р	0.7	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	0.4	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	183	°C/W	
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{\theta JA}$	115	C/VV	
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	Б	1.3	W	
Total Power Dissipation (Note 7)	$T_A = +70^{\circ}C$	P_{D}	0.8	VV	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State		94		
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	61	°C/W	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	39		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

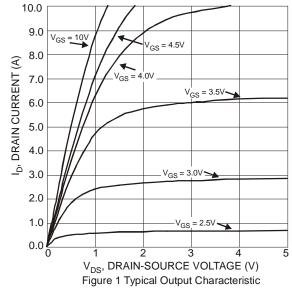
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

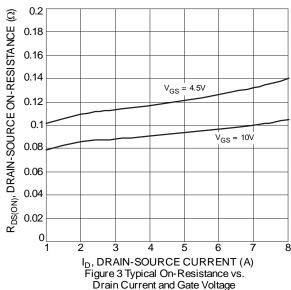
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)				·		
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance			92	140	mΩ	$V_{GS} = 10V, I_D = 1.8A$
Static Drain-Source On-Resistance	R _{DS(ON)}		115	170	11122	$V_{GS} = 4.5V, I_D = 1.3A$
Forward Transfer Admittance	Y _{fs}		2.2	_	S	$V_{DS} = 15V, I_{D} = 1.8A$
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V, I_S = 0.45A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}		315	_		V _{DS} = 40V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	Coss	_	18	_	pF	
Reverse Transfer Capacitance	Crss		16	_		
Gate Resistnace	R_g	_	0.65	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	8.6	_		
Total Gate Charge (V _{GS} = 5V)	Qg	_	4.1	_	nC	V 20V L 4.0A
Gate-Source Charge	Q _{gs}	_	1.0	_	nc	$V_{DS} = 30V, I_{D} = 1.8A$
Gate-Drain Charge	Q_{gd}	_	1.7	_		
Turn-On Delay Time	t _{D(on)}	_	2.6	_		
Turn-On Rise Time	t _r	_	3.6	_		$V_{DS} = 30V, V_{GS} = 10V,$ $R_G = 6.0\Omega, I_D = 1.8A$
Turn-Off Delay Time	t _{D(off)}	_	16.3	_	ns	
Turn-Off Fall Time	t _f	_	2.7	_		
Reverse Recovery Time	t _{rr}		16.8	_	ns	1 4 0 4 11/14 4 4 0 0 0 / 1 - 2
Reverse Recovery Charge	Qrr		9.0	_	$_{\rm nC}$ $_{\rm lf}$ = 1.8A, di/dt =100A/ μ s	

- 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1in. square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.

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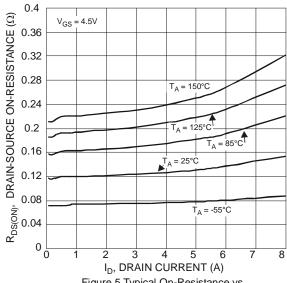
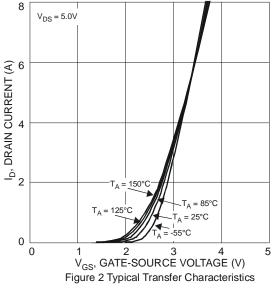
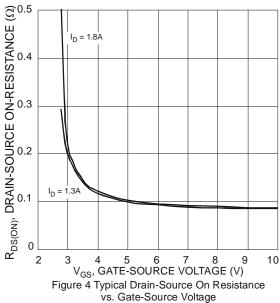
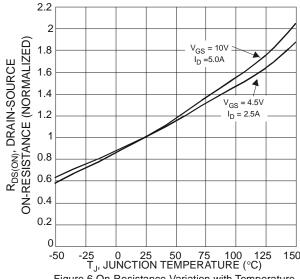


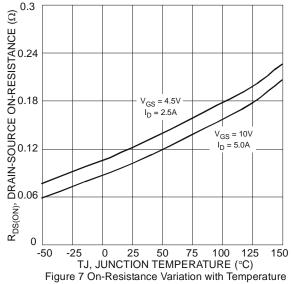
Figure 5 Typical On-Resistance vs. Drain Current and Temperature

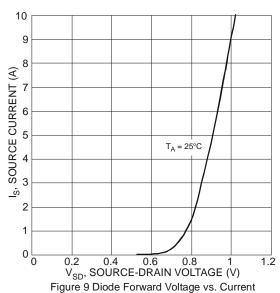


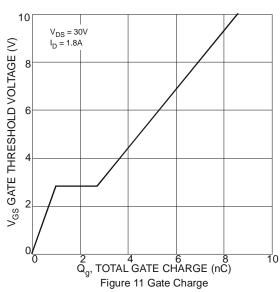












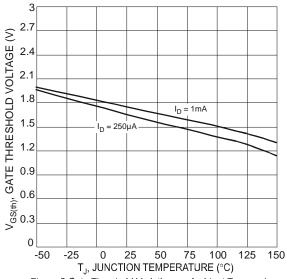
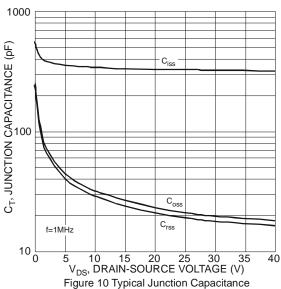


Figure 8 Gate Threshold Variation vs. Ambient Temperature



100

RDS(on)

RDS(on)

RDS(on)

RDS(on)

RDS(on)

RDS(on)

RDS(on)

Pw = 10µs

Pw = 10µs

Pw = 10ms

Pw = 100µs

Ta = 25°C

Vos = 10V

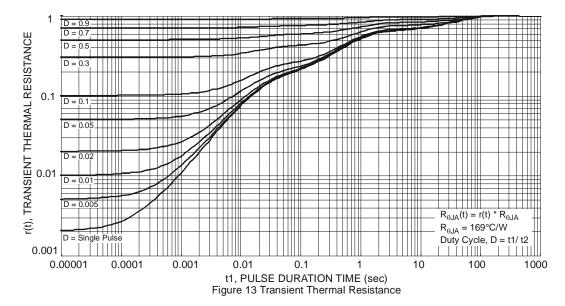
Single Pulse
DUT on 1*MRP board

0.001

VDS, DRAIN-SOURCE VOLTAGE (V)

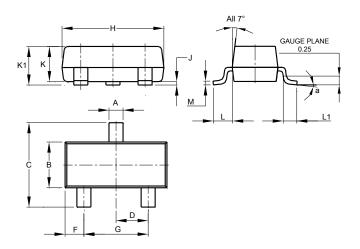
Figure 12 SOA, Safe Operation Area





Package Outline Dimensions

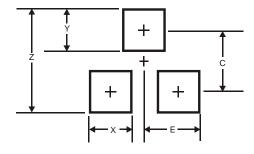
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
٦	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
α	8°							
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35



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